

CVD SILICON CARBIDE® Material Specification for Grades: SC-001, SC-002, SC-003

Properties

Crystal Structure

Sublimation Temperature (C)

Average Grain Size (µm)

Density (g cm⁻³)Hardness (kg mm⁻²)

Knoop (500 g load)

Vickers (500 g load)

Chemical Purity⁽²⁾Flexural Strength, (MPa/Ksi) 4-point⁽³⁾

@ RT

@ 1400°C

Weibull Parameters

Modulus, m

Scale Factor, β (MPa/Ksi)

Fracture Toughness, K_{IC} ValuesMicro-indentation (MN m^{-1.5})Controlled Flow (MN m^{-1.5})

Elastic Modulus

Sonic (GPa/10⁶ psi)4-point Flexure (GPa/10⁶ psi)Coefficient of Thermal Expansion (K⁻¹)

@ RT

@ RT to 1000°C

Heat Capacity(Jkg⁻¹ K⁻¹)

Poisson's Ratio

Polishability⁽⁴⁾Thermal Conductivity (Wm⁻¹ K⁻¹)

SC-001, SC-003

SC-002

Electrical Resistivity⁽⁵⁾ (Ωcm)

SC-002

SC-003

Typical Values⁽¹⁾

FCC(face-centered cubic);

polycrystalline, β-phase

~2700

5

3.21

2540

2500

≥99.9995% SiC

415/60

575/84

11

424/61

3.3

2.7

466/68

461/67

2.2 x 10⁻⁶4.0 x 10⁻⁶

640

0.21

<3Å RMS

300

285

<1

>1000

(1) Average values at room temperature unless otherwise specified.

(2) Total metallic impurities; detailed data on specific impurities is available on request.

(3) Flexure beams had a 0.5 µm RMS surface finish.

(4) Polishability was measured with an optical profilometer.

(5) Measured according to ASTM standard.

Solid CVD SILICON CARBIDE is an ultra-pure material with superior thermal and physical properties that are a result of Advanced Materials' bulk chemical vapor deposition (CVD) process. All three grades of CVD SILICON CARBIDE excel in high performance applications that require high temperature (>1500 °C), wear, and chemical resistance performance. Two grades provide controlled electrical resistivity properties: SC-002 Low Resistivity Grade (<1 Ωcm) and SC-003 High Resistivity Grade (>1,000 Ωcm); while the resistivity is not specified in the third grade, SC-001 Standard Grade.

Rev. 2, 09/2000